

# High Voltage NPN Silicon Power Transistors

## TIP47G, TIP48G, TIP50G

This series is designed for line operated audio output amplifier, SWITCHMODE power supply drivers and other switching applications.

### Features

- Popular TO-220 Plastic Package
- Complementary to the MJE5730 and MJE5731 Series
- These Devices are Pb-Free and are RoHS Compliant\*

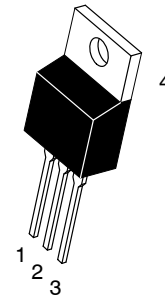
### MAXIMUM RATINGS

Symbol	Rating	TIP47	TIP48	TIP50	Unit
$V_{CEO}$	Collector – Emitter Voltage	250	300	400	Vdc
$V_{CB}$	Collector – Base Voltage	350	400	500	Vdc
$V_{EB}$	Emitter – Base Voltage	5.0			Vdc
$I_C$	Collector Current – Continuous	1.0			Adc
$I_{CM}$	Collector Current – Peak	2.0			Adc
$I_B$	Base Current	0.6			Adc
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	40 0.32			W W/ $^\circ\text{C}$
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	2.0 0.016			W W/ $^\circ\text{C}$
E	Unclamped Inducting Load Energy (See Figure 8)	20			mJ
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-65 to +150			$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

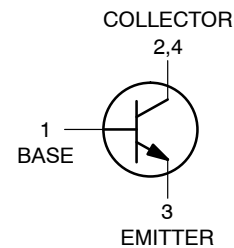
### THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3.125	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

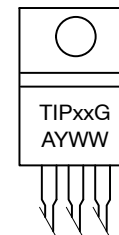


TO-220AB  
CASE 221A  
STYLE 1

## 1.0 AMPERE POWER TRANSISTORS NPN SILICON 250-300-400 VOLTS 40 WATTS



### MARKING DIAGRAM



TIPxx = Device Code  
 xx = 47, 48, or 50  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, [SOLDERRM/D](http://www.onsemi.com/SOLDERRM/D).

# TIP47G, TIP48G, TIP50G

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
--------	----------------	-----	-----	------

### OFF CHARACTERISTICS

$V_{CEO(sus)}$	Collector–Emitter Sustaining Voltage (Note 1) ( $I_C = 30\text{ mAdc}$ , $I_B = 0$ )	TIP47 TIP48 TIP50	250 300 400	– – –	Vdc
$I_{CEO}$	Collector Cutoff Current ( $V_{CE} = 150\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 200\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 300\text{ Vdc}$ , $I_B = 0$ )	TIP47 TIP48 TIP50	– – –	1.0 1.0 1.0	mAdc
$I_{CES}$	Collector Cutoff Current ( $V_{CE} = 350\text{ Vdc}$ , $V_{BE} = 0$ ) ( $V_{CE} = 400\text{ Vdc}$ , $V_{BE} = 0$ ) ( $V_{CE} = 500\text{ Vdc}$ , $V_{BE} = 0$ )	TIP47 TIP48 TIP50	– – –	1.0 1.0 1.0	mAdc
$I_{EBO}$	Emitter Cutoff Current ( $V_{BE} = 5.0\text{ Vdc}$ , $I_C = 0$ )		–	1.0	mAdc

### ON CHARACTERISTICS (Note 1)

$h_{FE}$	DC Current Gain ( $I_C = 0.3\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ )	30 10	150 –	–
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage ( $I_C = 1.0\text{ Adc}$ , $I_B = 0.2\text{ Adc}$ )	–	1.0	Vdc
$V_{BE(on)}$	Base–Emitter On Voltage ( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ )	–	1.5	Vdc

### DYNAMIC CHARACTERISTICS

$f_T$	Current–Gain – Bandwidth Product ( $I_C = 0.1\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 2.0\text{ MHz}$ )	10	–	MHz
$h_{fe}$	Small–Signal Current Gain ( $I_C = 0.2\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	25	–	–

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# TIP47G, TIP48G, TIP50G

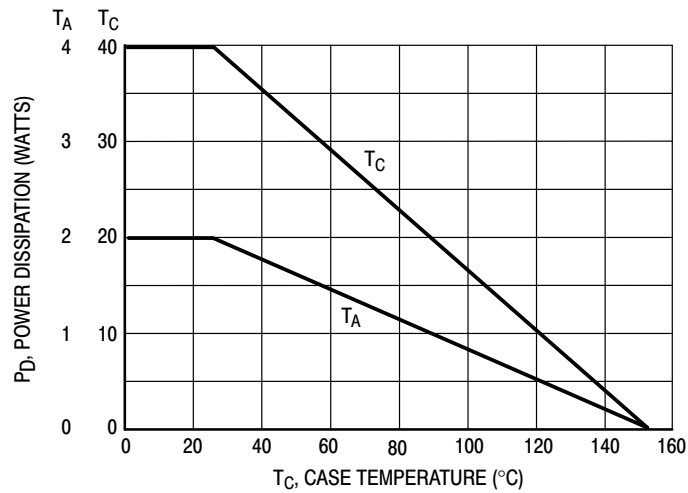
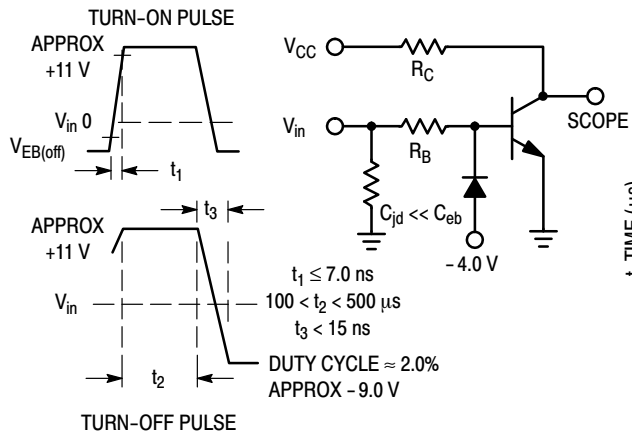


Figure 1. Power Derating



$R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 2. Switching Time Equivalent Circuit

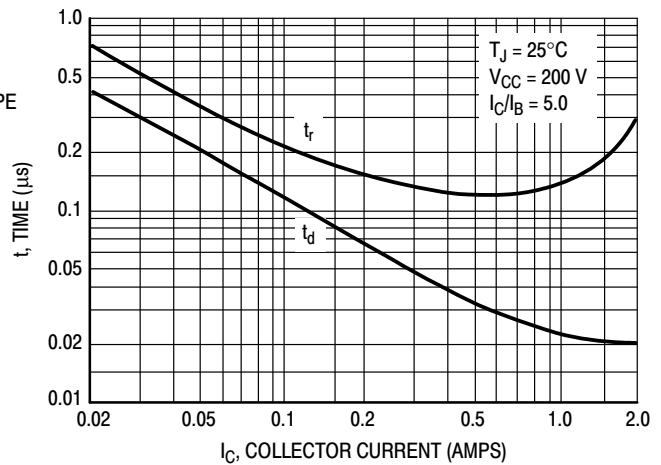


Figure 3. Turn-On Time

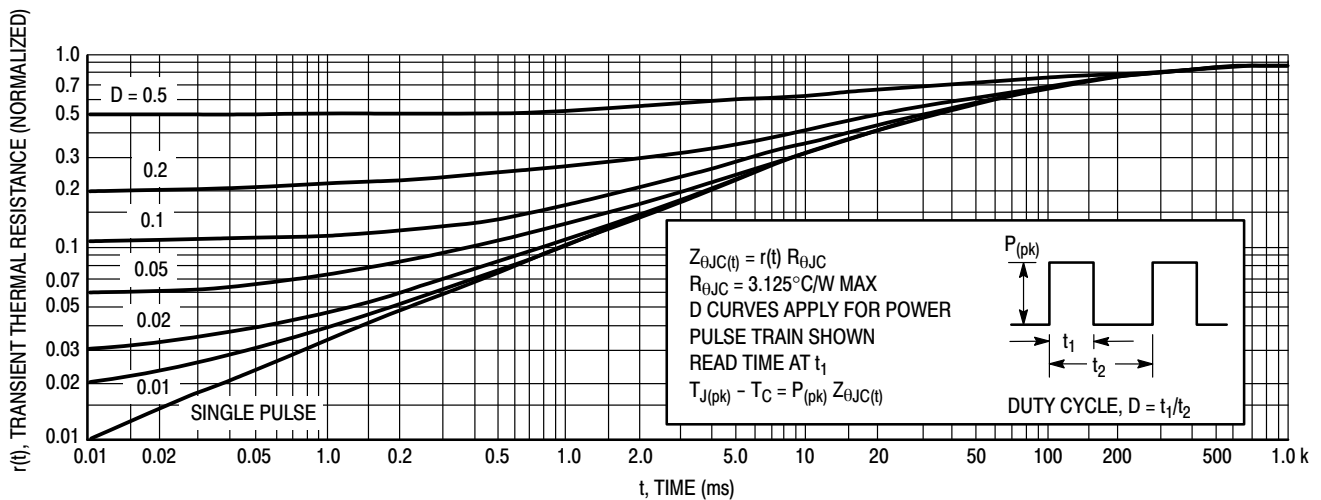


Figure 4. Thermal Response

## TIP47G, TIP48G, TIP50G

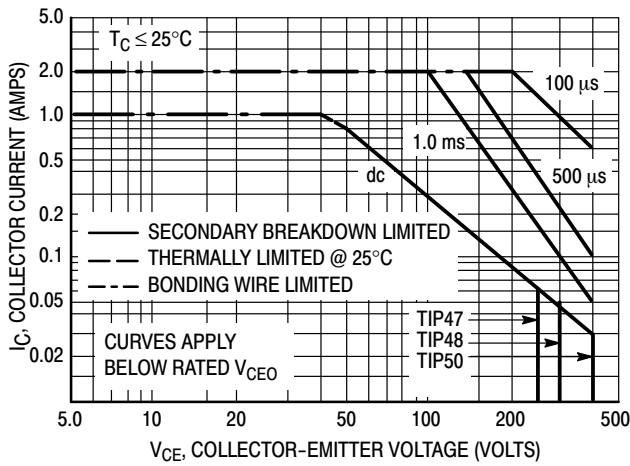


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

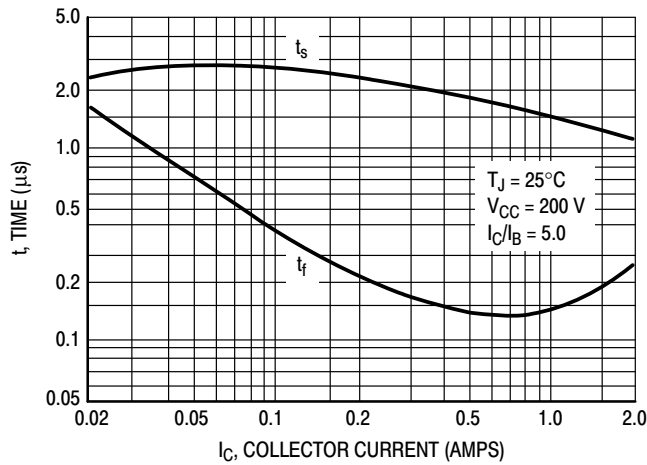


Figure 6. Turn-Off Time

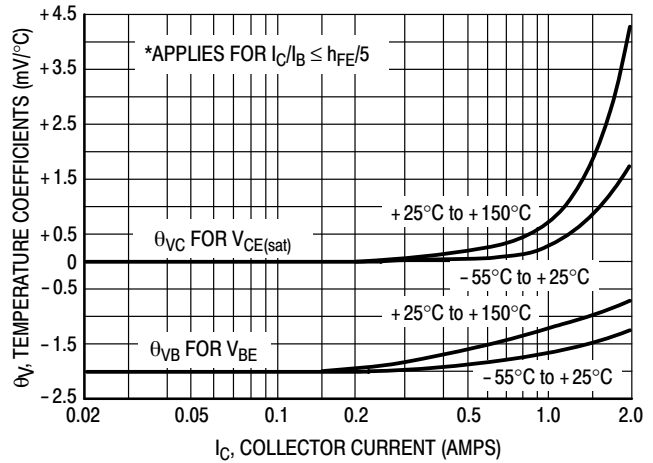
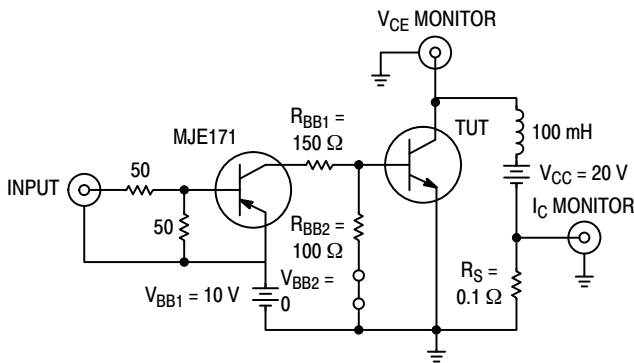


Figure 7. Temperature Coefficients



Note A: Input pulse width is increased until  $I_{CM} = 0.63\text{ A}$ .

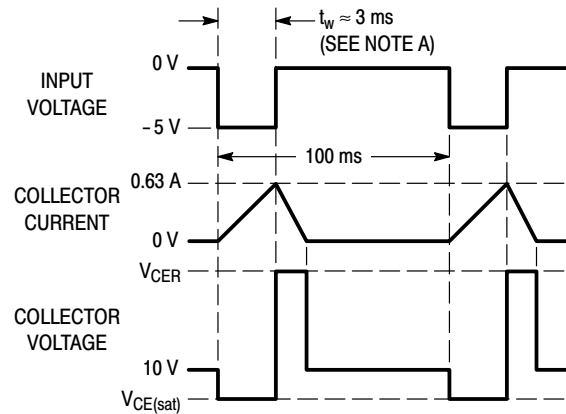


Figure 8. Inductive Load Switching

## TIP47G, TIP48G, TIP50G

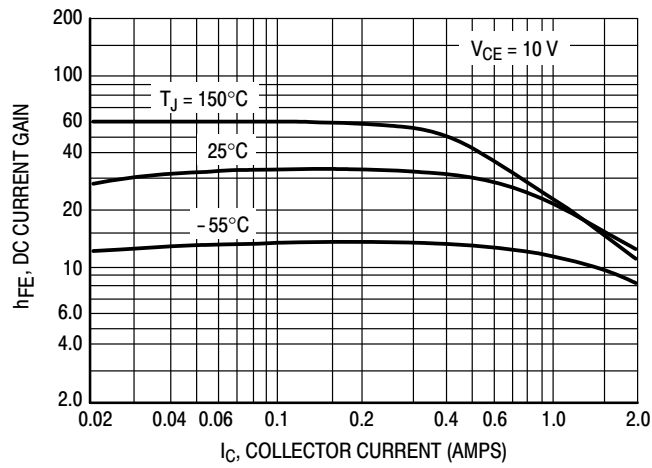


Figure 9. DC Current Gain

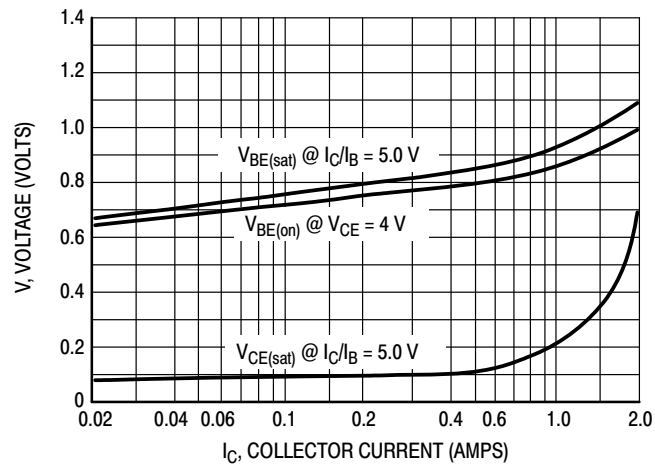


Figure 10. "On" Voltages

### ORDERING INFORMATION

Device	Package	Shipping
TIP47G	TO-220 (Pb-Free)	50 Units / Rail
TIP48G	TO-220 (Pb-Free)	50 Units / Rail
TIP49G	TO-220 (Pb-Free)	50 Units / Rail
TIP50G	TO-220 (Pb-Free)	50 Units / Rail

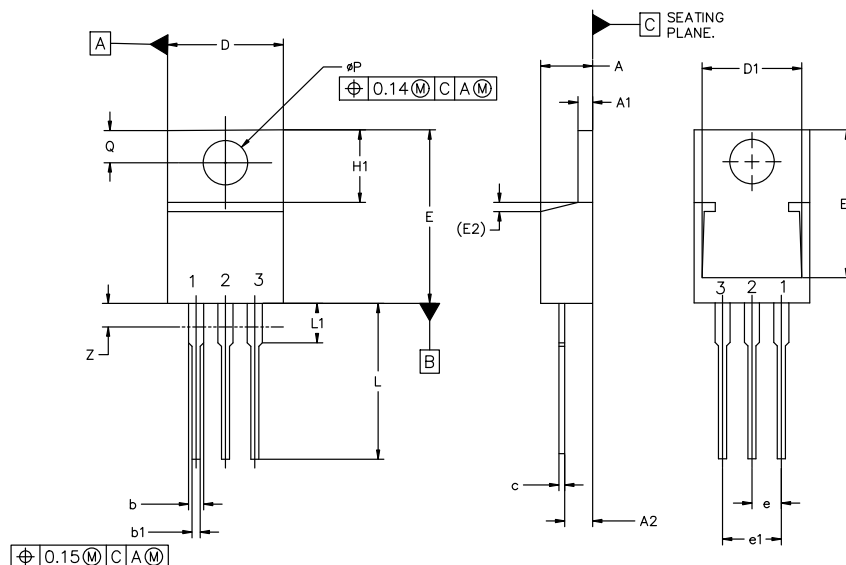


TO-220-3 10.10x15.12x4.45, 2.54P

CASE 221A

ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	---	---	3.48

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

STYLE 3:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:  
PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 10:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

DOCUMENT NUMBER:	98ASB42148B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-220-3 10.10x15.12x4.45, 2.54P	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)